

SANYO Semiconductors DATA SHEET

SBS818 — Low VF Schottky Barrier Diode 30V, 2.0A Rectifier

Applications

· High frequency rectification (switching regulators, converters, choppers).

Features

- · Small switching noise.
- Low forward voltage (IF=2.0A, VF max=0.52V)
- · Ultrasmall package permitting applied sets to be small and slim (Mounting height 0.75mm).

Specifications

Absolute Maximum Ratings at Ta=25°C (Value per element)

Parameter	Symbol	Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	VRRM		30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM		30	V
Average Output Current	10	When mounted on ceramic substrate	2.0	А
		When mounted on glass epoxy substrate	1.5	Α
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	20	А
Junction Temperature	Tj		-55 to +125	°C
Storage Temperature	Tstg		-55 to +125	°C

Marking: SD

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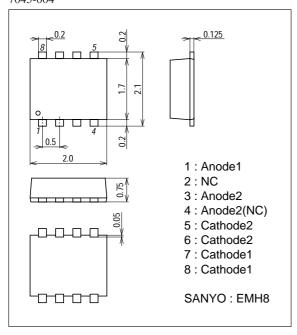
^{*:} The absolute maximum ratings and electrical characteristics refer to those between Terminal 1 and Terminal 7 (or 8), and between Terminal 3 and Terminal 5 (or 6).

Electrical Characteristics at Ta=25°C (Value per element)

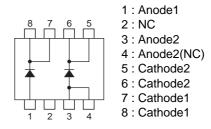
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Uniil
Reverse Voltage	٧R	IR=1mA	30			V
Forward Voltage	V _F 1	IF=1.0A		0.37		V
	V _F 2	IF=1.5A		0.42	0.47	V
	VF3	IF=2.0A		0.46	0.52	V
Reverse Current	IR	V _R =15V			350	μΑ
Interterminal Capacitance	С	V _R =10V, f=1MHz		30		pF
Reverse Recovery Time	t _{rr}	I _F =I _R =100mA, See specified Test Circuit.			10	ns
Thermal Resistance	Rth(j-a)1	When mounted in Cu-foiled area of		100		°C/W
		0.96mm ² ×0.03mm on glass epoxy substrate				
	Rth(j-a)2	When mounted on ceramic substrate (900mm²X0.8mm)		65		°C/W

Package Dimensions

unit : mm (typ) 7045-004



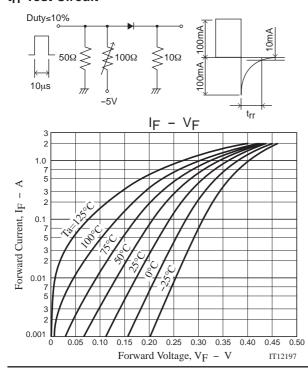
Electrical Connection

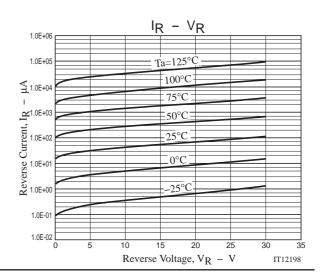


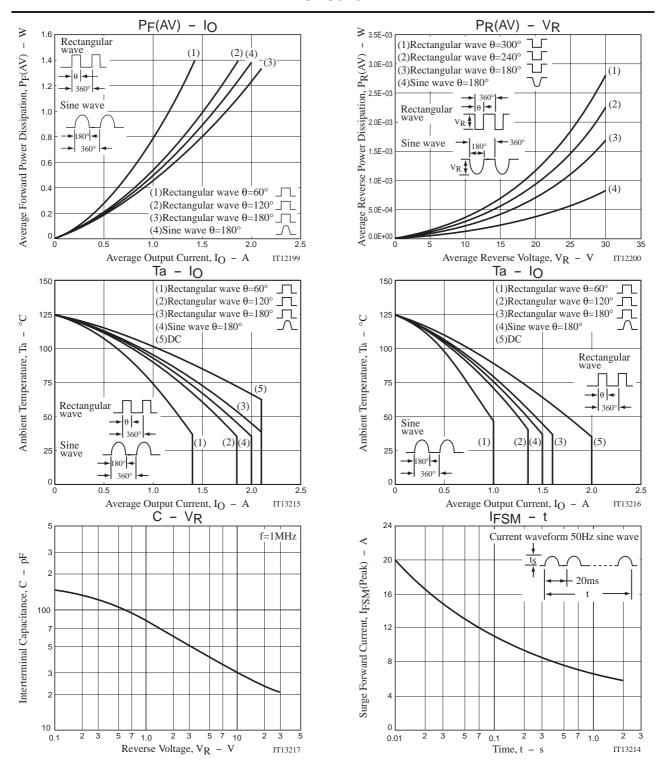
Top view

*: Terminal 4 is used for the purposes such as test. Although it is connected to Anode 2, please handle it as NC Terminal

trr Test Circuit







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